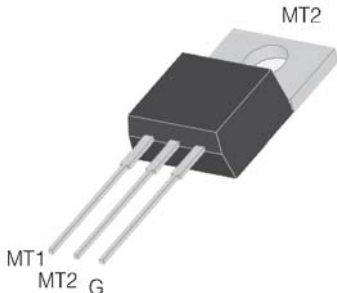
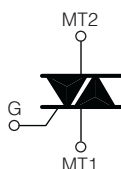


LOGIC LEVEL TRIAC

| | | | | | | | | | |
|-------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------|-----------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------|-------------------------|-----------------------------|-------|---------|--------------------------|--|---------------|--|
| <p style="text-align: center;">TO-220A B</p>   | <table style="width: 100%; border-collapse: collapse;"> <tr> <td style="width: 50%; text-align: center;">On-State Current</td> <td style="width: 50%; text-align: center;">Gate Trigger Current</td> </tr> <tr> <td style="text-align: center;">8 Amp</td> <td style="text-align: center;">< 10 mA</td> </tr> <tr> <td colspan="2" style="text-align: center;">Off-State Voltage</td> </tr> <tr> <td colspan="2" style="text-align: center;">200 V ÷ 800 V</td> </tr> </table> <p>This series of TRIACs uses a high performance PNPN technology.</p> <p>These parts are intended for general purpose AC switching applications with highly inductive loads.</p> | On-State Current | Gate Trigger Current | 8 Amp | < 10 mA | Off-State Voltage | | 200 V ÷ 800 V | |
| On-State Current | Gate Trigger Current | | | | | | | | |
| 8 Amp | < 10 mA | | | | | | | | |
| Off-State Voltage | | | | | | | | | |
| 200 V ÷ 800 V | | | | | | | | | |

Absolute Maximum Ratings, according to IEC publication No. 134

| SYMBOL | PARAMETER | CONDITIONS | Value | Unit |
|--------------|-------------------------------------------|---------------------------------------------------------------------------------------------------------|---------------|------------------|
| $I_{T(RMS)}$ | RMS On-state Current (full sine wave) | All Conduction Angle, $T_C = 95\text{ }^\circ\text{C}$ | 8 | A |
| I_{TSM} | Non-repetitive On-State Current | Full Cycle, 60 Hz ($t = 16.7\text{ ms}$) | 88 | A |
| I_{TSM} | Non-repetitive On-State Current | Full Cycle, 50 Hz ($t = 20\text{ ms}$) | 80 | A |
| I^2t | Fusing Current | $t_p = 10\text{ ms}$, Half Cycle | 32 | A^2s |
| I_{GM} | Peak Gate Current | $20\text{ }\mu\text{s max.}$ $T_j = 125\text{ }^\circ\text{C}$ | 4 | A |
| $P_{G(AV)}$ | Average Gate Power Dissipation | $T_j = 125\text{ }^\circ\text{C}$ | 1 | W |
| di/dt | Critical rate of rise of on-state current | $I_G = 2x I_{GT}$, $t_r \leq 100\text{ ns}$ $f = 120\text{ Hz}$, $T_j = 125\text{ }^\circ\text{C}$ | 50 | $A/\mu\text{s}$ |
| T_j | Operating Temperature | | $(-40 + 125)$ | $^\circ\text{C}$ |
| T_{stg} | Storage Temperature | | $(-40 + 150)$ | $^\circ\text{C}$ |
| T_{sld} | Soldering Temperature | 10s max | 260 | $^\circ\text{C}$ |

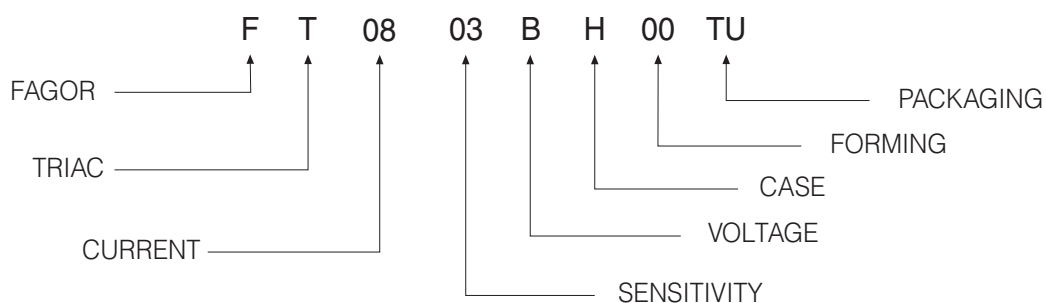
| SYMBOL | PARAMETER | VOLTAGE | | | | | Unit |
|-----------|-----------------------------------|---------|-----|-----|-----|-----|------|
| | | B | D | M | S | N | |
| V_{DRM} | Repetitive Peak Off State Voltage | 200 | 400 | 600 | 700 | 800 | V |
| V_{RRM} | | | | | | | |

LOGIC LEVEL TRIAC
Electrical Characteristics

| SYMBOL | PARAMETER | CONDITIONS | Quadrant | | SENSITIVITY | | | | | Unit |
|------------------------------------|----------------------------------------|--------------------------------------------------------------------------------------------------------------------------------------------------------------|----------|-----|-------------|-----|-----|-----|-----|------|
| | | | | | 03 | 04 | 07 | 08 | 09 | |
| I _{GT} ⁽¹⁾ | Gate Trigger Current | V _D = 12 V _{DC} , R _L = 33Ω, T _j = 25 °C | Q1÷Q3 | MAX | 3 | 5 | 5 | 10 | 10 | mA |
| | | | Q4 | MAX | 5 | | 7 | | 10 | mA |
| V _{GT} | Gate Trigger Voltage | V _D = 12 V _{DC} , R _L = 33Ω, T _j = 25 °C | Q1÷Q3 | MAX | 1.3 | | | | | V |
| | | | Q1÷Q4 | MAX | 1.3 | | | | | V |
| V _{GD} | Gate Non Trigger Voltage | V _D = V _{DRM} , R _L = 3.3 KΩ, T _j = 125 °C | Q1÷Q3 | MIN | 0.2 | | | | | V |
| | | | Q1÷Q4 | MIN | 0.2 | | | | | V |
| I _H ⁽²⁾ | Holding Current | I _T = 100 mA, Gate open, T _j = 25 °C | | MAX | 7 | 15 | 15 | 15 | 20 | mA |
| I _L | Latching Current | I _G = 1.2 I _{GT} , T _j = 25 °C | Q1,Q3 | MAX | | 25 | | 25 | | mA |
| | | | Q1,Q3,Q4 | MAX | 7 | | 20 | | 20 | mA |
| | | | Q2 | MAX | 20 | 30 | 30 | 30 | 25 | mA |
| dV/dt ⁽²⁾ | Critical Rate of Voltage Rise | V _D = 0.67 x V _{DRM} , Gate open T _j = 125 °C | | MIN | 10 | 40 | 20 | 40 | 50 | V/μs |
| (dI/dt) ⁽²⁾ | Critical Rate of Current Rise | (dv/dt) _c = 0.1 V/μs T _j = 125 °C (dv/dt) _c = 10 V/μs T _j = 125 °C without snubber T _j = 125 °C | | MIN | 1.2 | 5.4 | 3.5 | 5.4 | 2.5 | A/ms |
| | | | | MIN | 0.6 | 2.8 | 1.5 | 2.8 | 1.5 | A/ms |
| | | | | MIN | | | | | | |
| V _{TM} ⁽²⁾ | On-state Voltage | I _T = 11 Amp, t _p = 380 μs, T _j = 25 °C | | MAX | 1.6 | | | | | V |
| V _{t(o)} ⁽²⁾ | Threshold Voltage | T _j = 125 °C | | MAX | 0.85 | | | | | V |
| r _d ⁽²⁾ | Dynamic resistance | T _j = 125 °C | | MAX | 50 | | | | | mΩ |
| I _{DRM} /I _{RRM} | Off-State Leakage Current | V _D = V _{DRM} , T _j = 125 °C | | MAX | 1 | | | | | mA |
| | | V _R = V _{RRM} , T _j = 25 °C | | MAX | 5 | | | | | μA |
| R _{th(j-c)} | Thermal Resistance Junction-Case | for AC 360° conduction angle | | | 1.6 | | | | | °C/W |
| R _{th(j-a)} | Thermal Resistance Junction-Ambient | S = 1 cm ² | | | 60 | | | | | °C/W |

(1) Minimum I_{GT} is guaranteed at 5% of I_{GT} max.

(2) For either polarity of electrode MT2 voltage with reference to electrode MT1.

PART NUMBER INFORMATION


LOGIC LEVEL TRIAC

Fig. 1: Maximum power dissipation versus RMS on-state current (full cycle).

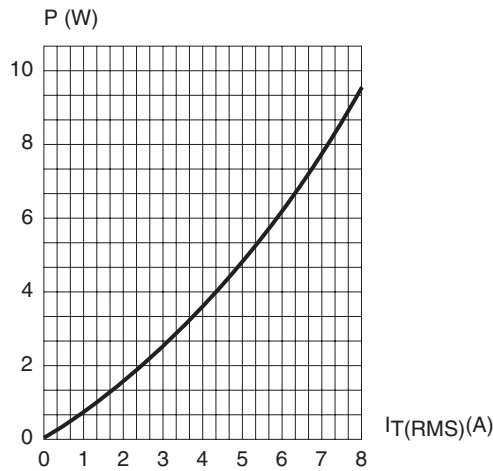


Fig. 2: RMS on-state current versus case temperature (full cycle).

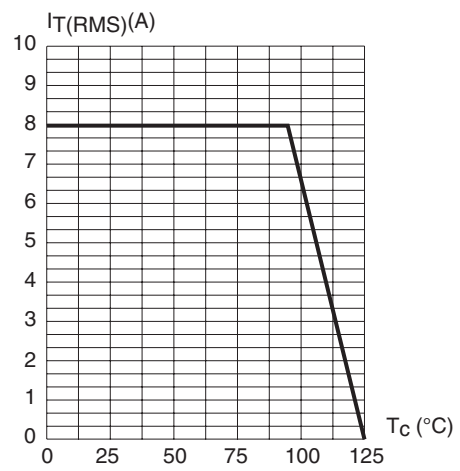


Fig. 3: Relative variation of thermal impedance versus pulse duration.

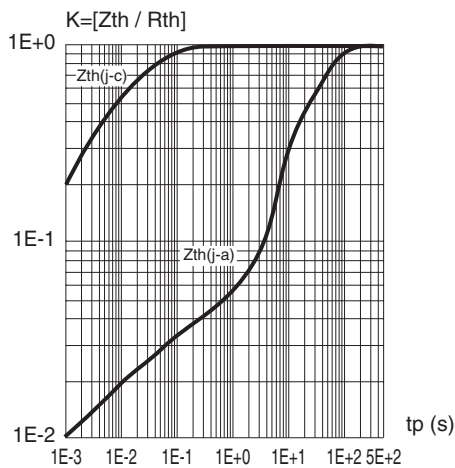


Fig. 4: On-state characteristics (maximum values)

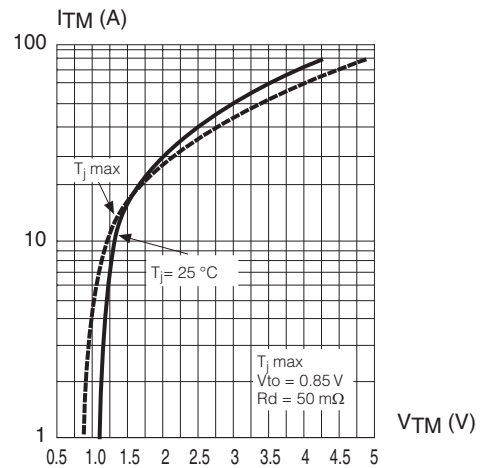


Fig. 5: Surge peak on-state current versus number of cycles

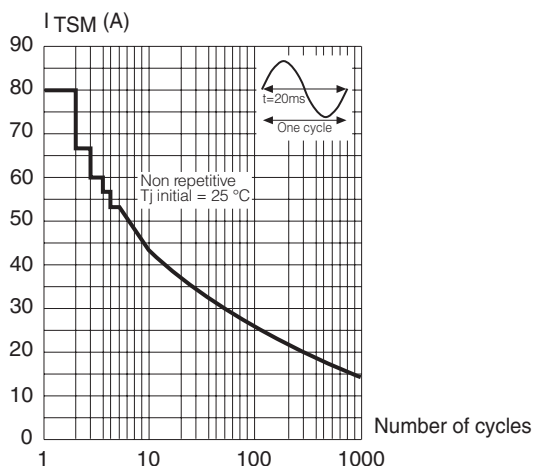
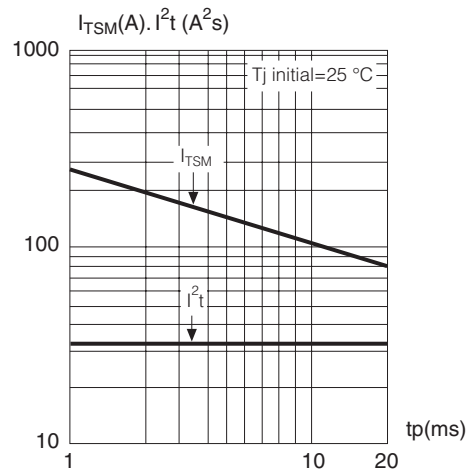


Fig. 6: Non repetitive surge peak on-state current for a sinusoidal pulse with width: $t_p < 10$ ms, and corresponding value of I^2t .



LOGIC LEVEL TRIAC

Fig. 7: Relative variation of gate trigger current, holding current and latching versus junction temperature (typical values)

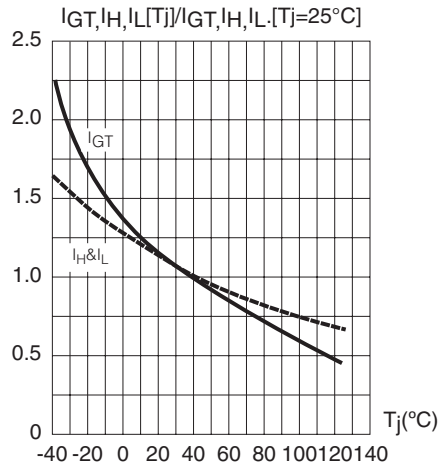


Fig. 8: Relative variation of critical rate of decrease of main current versus junction temperature

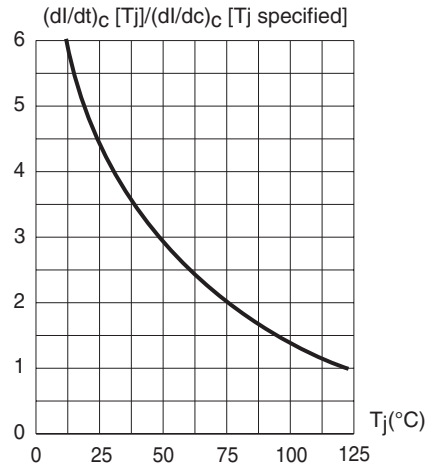
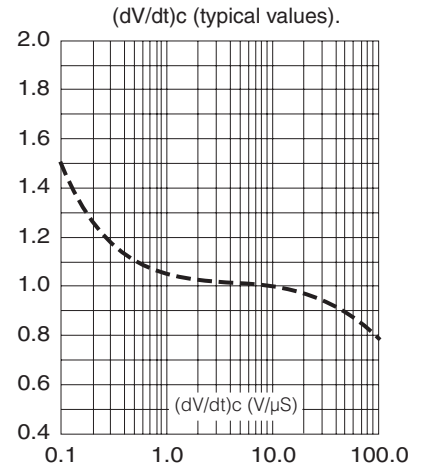
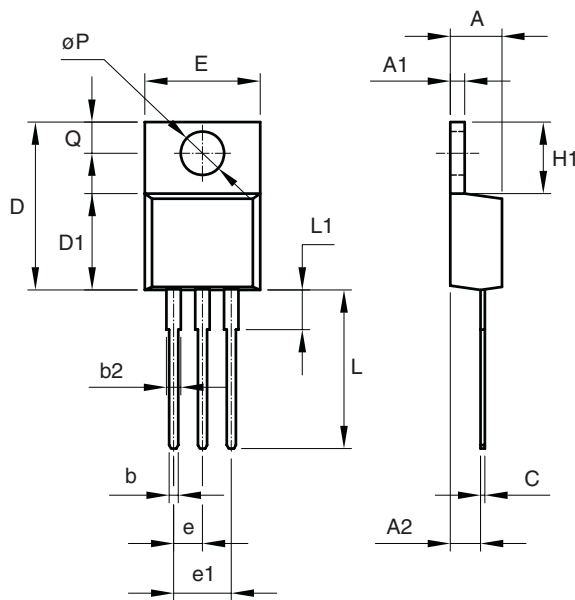


Fig. 9: Relative variation of critical rate of decrease of main current versus



PACKAGE MECHANICAL DATA

TO-220AB



| REF. | DIMENSIONS | |
|------|-------------|-------|
| | Millimeters | |
| | Min. | Max. |
| A | 4.47 | 4.67 |
| A1 | 1.17 | 1.37 |
| A2 | 2.52 | 2.82 |
| b | 0.71 | 0.91 |
| b2 | 1.17 | 1.37 |
| c | 0.31 | 0.53 |
| D | 14.65 | 15.35 |
| D1 | 8.50 | 8.90 |
| E | 10.01 | 10.36 |
| e | 2.51 | 2.57 |
| e1 | 4.98 | 5.18 |
| H1 | 6.15 | 6.45 |
| L | 13.40 | 13.96 |
| L1 | 3.56 | 3.96 |
| P | 3.735 | 3.935 |
| Q | 2.59 | 2.89 |

Mounting Torque

1 N.m

(*) Limiting values and life support applications, see Web page.